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IN THE SPECIFICATION:

Please amend the specification as follows:

Please amend the second paragraph on page 5 as follows:

To attain the object, a first method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a substrate; forming an insulating film such that the conductive film is covered with the insulating film; forming, in the insulating film, a hole having a bottom portion not reaching the conductive film by using a mask layer having a first opening pattern; and forming, in the insulating film, an opening for exposing the conductive film by using a mask layer having a second opening pattern having an opening diameter larger than an opening diameter of the first opening pattern, an obtuse angle being formed between a wall surface of the opening and a bottom surface of the opening.

Please amend the last paragraph on page 7 as follows:

A second method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a specified region of a substrate; forming an insulating film on the substrate such that the conductive film is covered with the insulating film; forming, on the insulating film, a mask layer having a first opening pattern above the conductive film; performing first etching with respect to the insulating film by using the mask layer having the first opening pattern to form, in the insulating film, a depressed portion having a bottom portion not reaching the conductive film; forming a mask layer having a second opening pattern having an opening diameter larger than an opening diameter of the first opening

pattern by enlarging the opening diameter of the first opening pattern; and performing second etching with respect to the insulating film by using the mask layer having the second opening pattern to form, in the insulating film, an opening for exposing the conductive film such that the opening has a diameter larger than a diameter of the depressed portion and a wall surface having a tapered configuration.

Please amend the last paragraph on page 9 as follows:

Preferably, the second method for fabricating a semiconductor device further comprises, after the step of forming the opening in the insulating film, the steps of: forming a mask layer having a third opening pattern having an opening diameter larger than the opening diameter of the second opening pattern by enlarging the opening diameter of the second opening pattern; and performing third etching with respect to the insulating film by using the mask layer having the third opening pattern to smooth the tapered configuration of the wall surface of the opening.

Please amend the last paragraph on page 10 as follows:

A third method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a specified region of a substrate; forming an etching stopper film on the conductive film; forming an insulating film on the substrate such that the etching stopper film is covered with the insulating film; forming, on the insulating film, a mask layer having a first opening pattern above the conductive film; performing first etching with respect to the insulating film by using the mask layer having the first opening pattern to form, in the insulating film, a depressed portion having a bottom portion not reaching the etching

stopper film; forming a mask layer having a second opening pattern having an opening diameter larger than an opening diameter of the first opening pattern by enlarging the opening diameter of the first opening pattern; performing second etching with respect to the insulating film by using the mask layer having the second opening pattern to form, in the insulating film, an opening for exposing the etching stopper film such that the opening has a diameter larger than a diameter of the depressed portion and a wall surface having a tapered configuration; and performing third etching with respect to the etching stopper film to transfer the opening of the insulating film to the etching stopper film and thereby form, in the etching stopper film, an opening for exposing the conductive film, while smoothing the tapered configuration of the wall surface of the opening of the insulating film.

Please amend fifth paragraph on page 12 as follows:

In the third method for fabricating a semiconductor device, the third etching is preferably performed by using a mask layer having a third opening pattern formed by enlarging the opening diameter of the second opening pattern.

Please amend the fourth paragraph on page 13 as follows:

A fourth method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a specified region of a substrate; forming an insulating film on the substrate such that the conductive film is covered with the insulating film; forming, on the insulating film, a mask layer having a first opening pattern above

the conductive film; performing first etching with respect to the insulating film by using the mask layer having the first opening pattern to form, in the insulating film, a depressed portion having a bottom portion not reaching the conductive film; and, after removing the mask layer, performing second etching with respect to an entire surface of the insulating film to form, in the insulating film, an opening for exposing the conductive film such that the opening has a diameter larger than a diameter of the depressed portion and a wall surface having a tapered configuration.